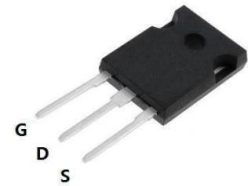


## N-CHANNEL SiC POWER MOSFET

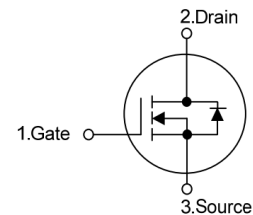
### Features

- $R_{DS(on)}=80m\Omega$ (Typ.) @  $V_{GS}=20V, I_D=20A$
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitance
- Easy to Parallel and Simple to Drive



### Applications

- Renewable Energy
- DC/DC converters
- EV Battery Chargers
- Switch Mode Power Supplies
- Solar Inverters



### Key Performance and Package Parameters

| Order codes     | $V_{DS}$ | $I_D$ | $R_{DS(ON)}$ , Typ | $T_{vjmax}$     | Marking    | Package |
|-----------------|----------|-------|--------------------|-----------------|------------|---------|
| XC080M120A1S3-A | 1200V    | 20A   | 80m $\Omega$       | 150 $^{\circ}C$ | C80M120A1A | TO247-3 |

### Absolute Maximum Ratings ( $T_c=25^{\circ}C$ unless otherwise specified.)

| Symbol      | Parameter                                       | Value      | Units       |
|-------------|---|------------|-------------|
| $V_{DSS}$   | Drain-Source Voltage                            | 1200       | V           |
| $V_{GSmax}$ | Absolute maximum Gate-Source Voltage            | -10/+25    | V           |
| $V_{GSop}$  | Recommended operational Gate-Source Voltage     | -5/+20     | V           |
| $I_D$       | Continuous Drain Current ( $T_c=25^{\circ}C$ )  | 41         | A           |
| $I_{DM}$    | Pulsed Drain Current                            | 80         | A           |
| $P_D$       | Maximum Power Dissipation ( $T_c=25^{\circ}C$ ) | 240        | W           |
| $T_J$       | Operating Junction Temperature Range            | -55 to 150 | $^{\circ}C$ |
| $T_{STG}$   | Storage Temperature Range                       | -55 to 150 | $^{\circ}C$ |

### Thermal Data

| Symbol          | Parameter   | Conditions | Max. | Units         |
|-----------------|---|------------|------|---------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Steady State) | TO247-3    | 0.52 | $^{\circ}C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient             | TO247-4    | 35.7 | $^{\circ}C/W$ |

**Electrical Characteristics** ( $T_c=25^{\circ}\text{C}$  unless otherwise specified.)

| Symbol       | Parameter                        | Conditions  | Min. | Typ. | Max. | Unit      |
|--------------|----------------------------------|---|------|------|------|-----------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage   | $V_{GS}=0V, I_{DS}=100\mu A$                                      | 1200 | ---  | ---  | V         |
| $I_{DSS}$    | Zero Gate Voltage Drain Current  | $V_{DS}=1200V, V_{GS}=0V$   | ---  | 1    | 100  | $\mu A$   |
| $I_{GSS}$    | Gate-Source Leakage Current      | $V_{GS}=20V, V_{DS}=0V$   | ---  | ---  | 250  | nA        |
| $V_{GS(th)}$ | Gate Threshold Voltage           | $V_{DS}=V_{GS}, I_{DS}=5mA$                                       | 2.0  | 2.3  | 4.0  | V         |
| $R_{DS(ON)}$ | Drain-Source On-state Resistance | $V_{GS}=20V, I_{DS}=20A$  | --   | 80   | 90   | $m\Omega$ |
| $Q_g$        | Total Gate Charge                | $V_{DS}=800V$   | ---  | 92   | ---  | nC        |
| $Q_{gs}$     | Gate-Source Charge               | $V_{GS}=-5V/20V$  | ---  | 15   | ---  | nC        |
| $Q_{gd}$     | Gate-Drain Charge                | $I_{DS}=20A$  | ---  | 45   | ---  | nC        |
| $t_{d(on)}$  | Turn-on Delay Time               | $V_{DD}=800V,$<br>$V_{GS}=-5V/20V$<br>$I_{DS}=20A, R_G=2.5\Omega$ | ---  | 18   | ---  | ns        |
| $t_r$        | Rise Time                        |   | ---  | 25   | --   | ns        |
| $t_{d(off)}$ | Turn-off Delay Time              |   | ---  | 28   | ---  | ns        |
| $t_f$        | Fall Time                        |   | ---  | 19   | ---  | ns        |
| $C_{iss}$    | Input Capacitance                | $V_{DS}=1000V$<br>$f=1MHz$  | ---  | 1601 | ---  | pF        |
| $C_{oss}$    | Output Capacitance               |   | ---  | 88   | ---  | pF        |
| $C_{rss}$    | Reverse Transfer Capacitance     |   | ---  | 28   | ---  | pF        |

**Reverse Diode Characteristics**

| Symbol    | Parameter                     | Conditions                                      | Min. | Typ. | Max. | Units |
|-----------|-------------------------------|---|------|------|------|-------|
| $V_{SD}$  | Diode Forward Voltage         | $I_{SD}=10A, V_{GS}=-5V$                        | ---  | 5.8  | ---  | V     |
| $t_{rr}$  | Diode Reverse Recovery Time   | $V_R=800V, I_{SD}=20A$<br>$di/dt=795.4 A/\mu s$ | ---  | 34   | ---  | ns    |
| $Q_{rr}$  | Diode Reverse Recovery Charge |   | ---  | 80   | ---  | nC    |
| $I_{rrm}$ | Peak Reverse Recovery Current |   | ---  | 5.3  | ---  | A     |

### Typical Characteristics

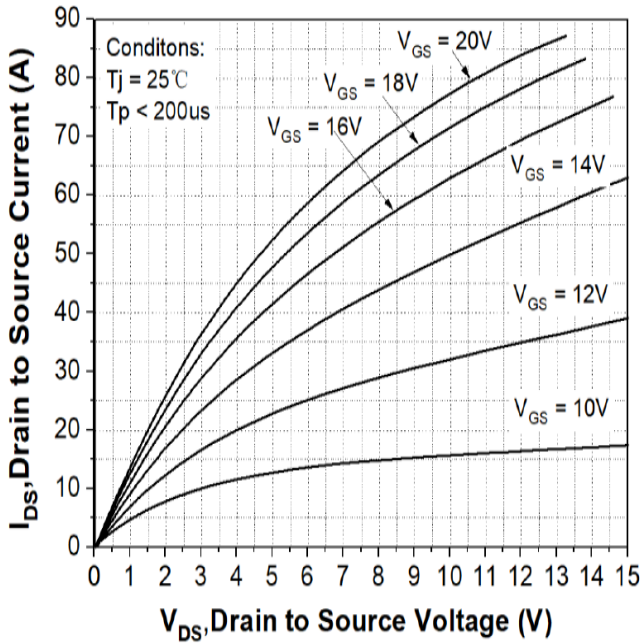


Fig.1 Output Characteristics

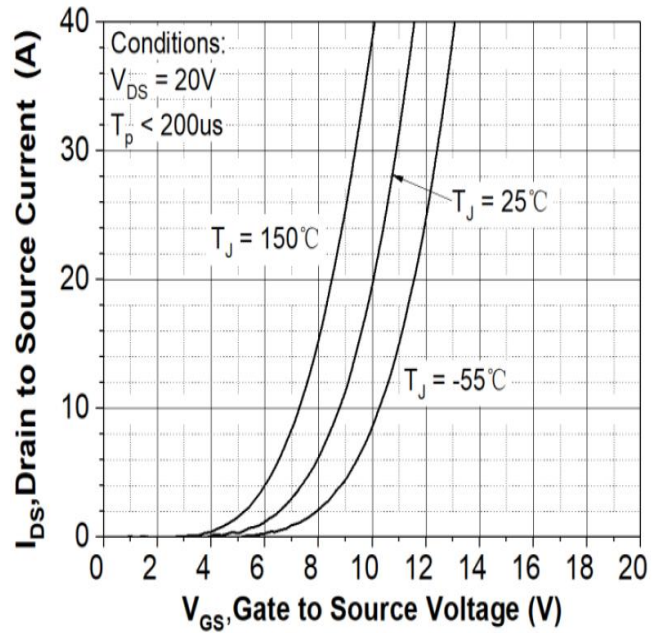


Fig.2 Output Characteristics

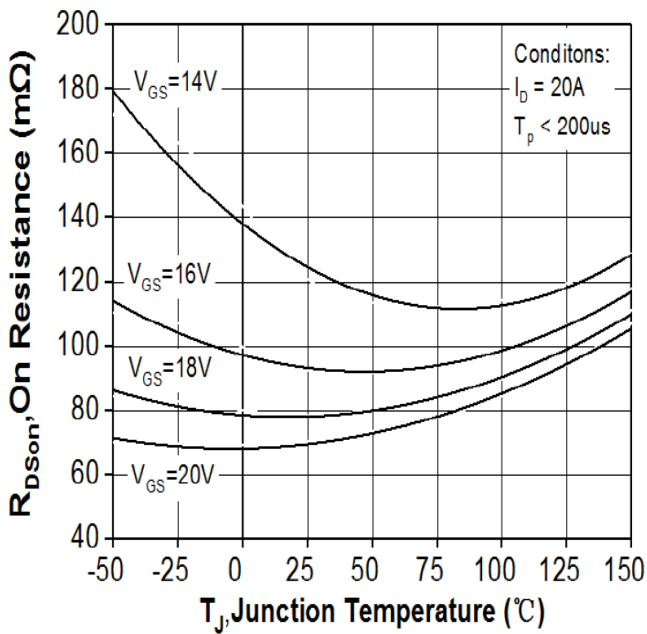


Fig.3 Drain-Source On Resistance

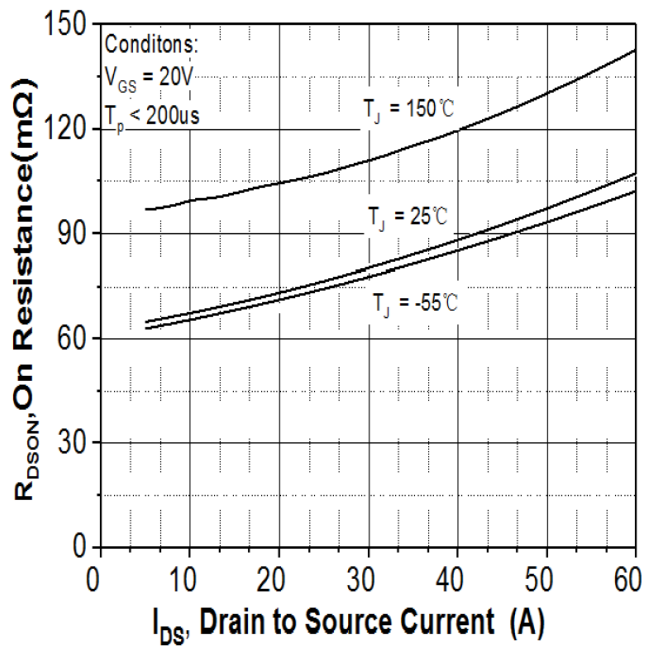


Fig.4 Drain-Source On Resistance

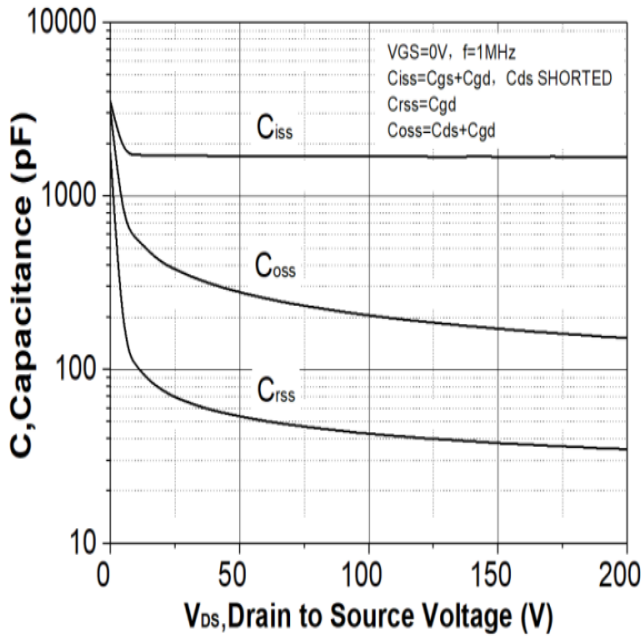


Fig.5 Capacitances (Voltage 0-200V)

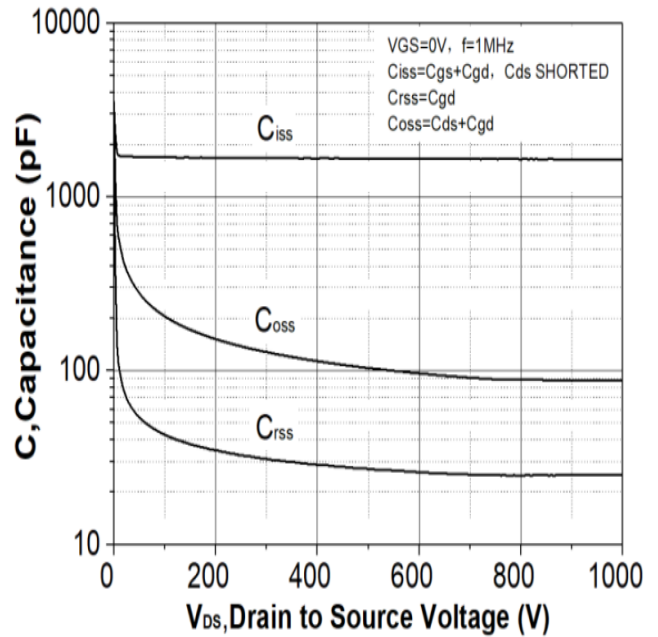


Fig.6 Capacitances (Voltage 0-1000V)

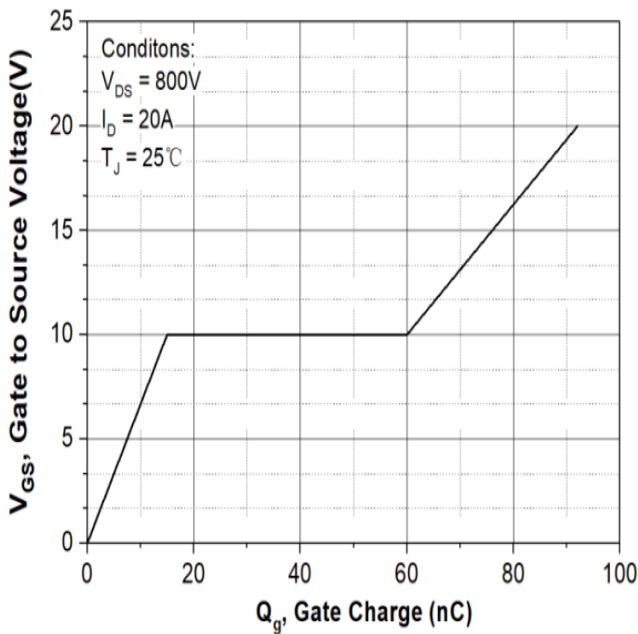


Fig.7 Gate charge characteristic

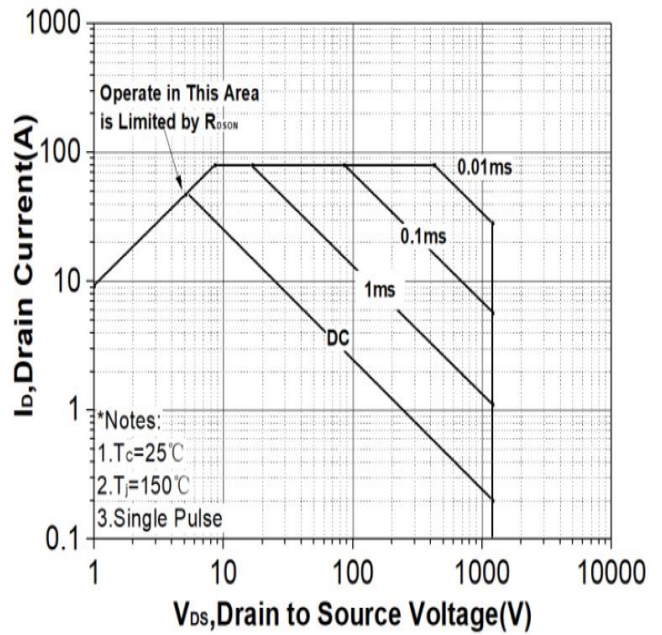


Fig.8 Safe Operating Area

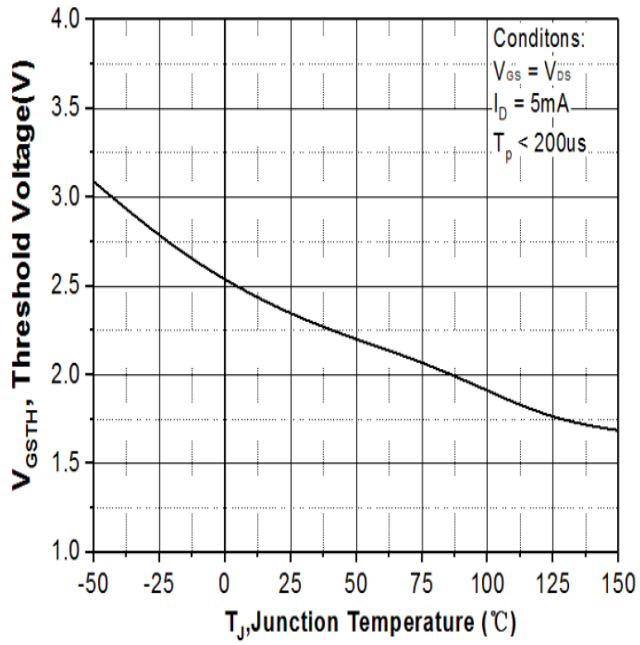


Fig.9 Threshold Voltage vs. Temperature

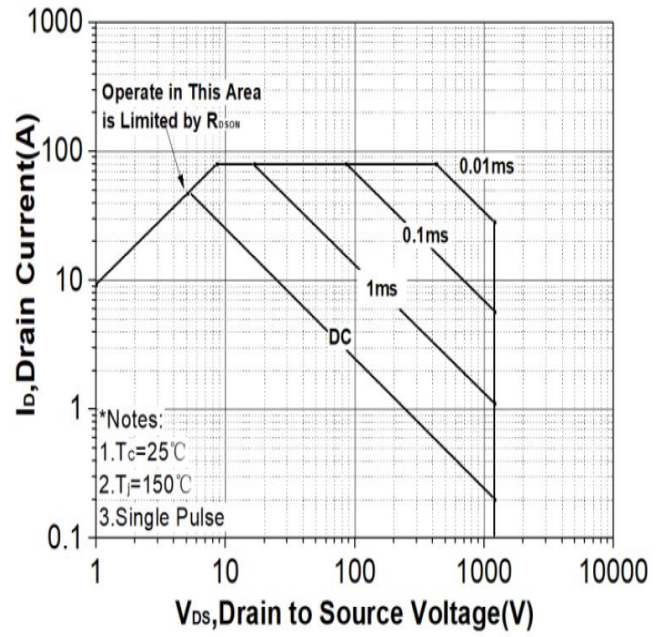
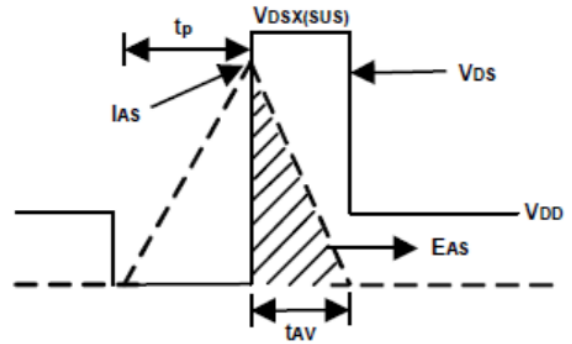
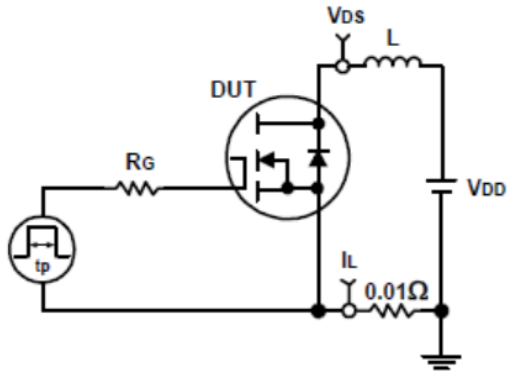
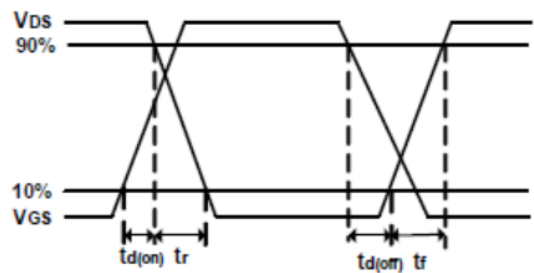
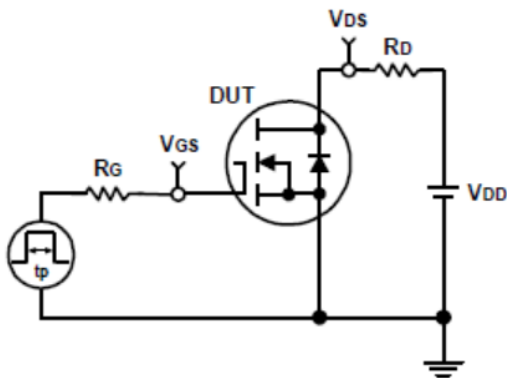


Fig.10 Output Capacitor Stored Energy

### Avalanche Test Circuit and Waveforms

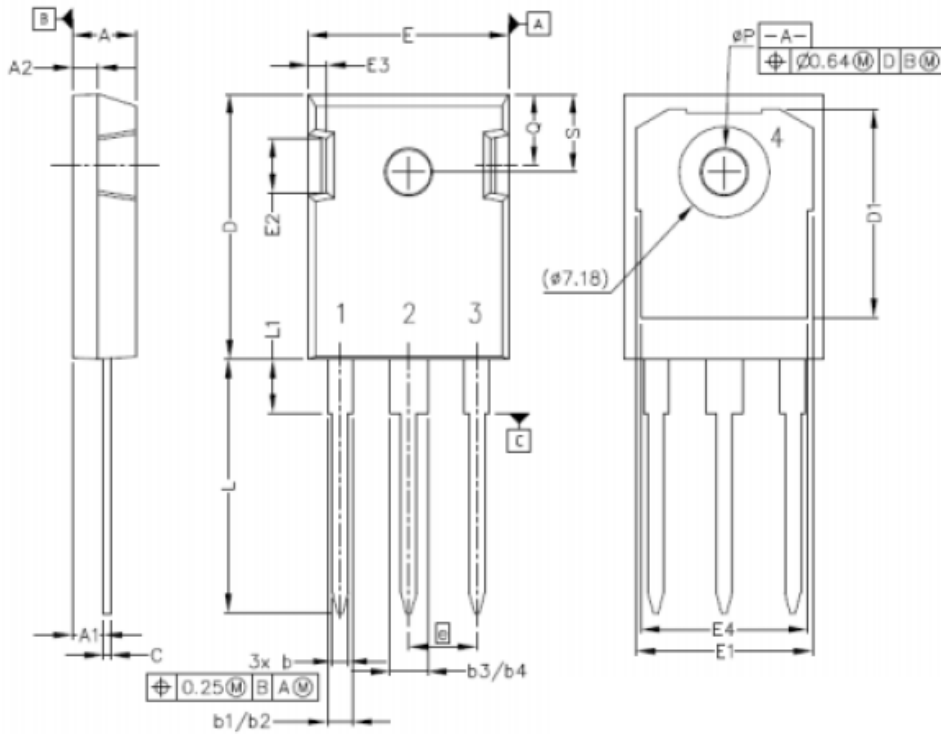


### Switching Time Test Circuit and Waveforms



### Package Information

TO-247-3



| POS | Inches   |      | Millimeters |       |
|-----|----------|------|-------------|-------|
|     | Min      | Max  | Min         | Max   |
| A   | .190     | .205 | 4.83        | 5.21  |
| A1  | .090     | .100 | 2.29        | 2.54  |
| A2  | .075     | .085 | 1.91        | 2.16  |
| b   | .042     | .052 | 1.07        | 1.33  |
| b1  | .075     | .095 | 1.91        | 2.41  |
| b2  | .075     | .085 | 1.91        | 2.16  |
| b3  | .113     | .133 | 2.87        | 3.38  |
| b4  | .113     | .123 | 2.87        | 3.13  |
| c   | .022     | .027 | 0.55        | 0.68  |
| D   | .819     | .831 | 20.80       | 21.10 |
| D1  | .640     | .695 | 16.25       | 17.65 |
| D2  | .037     | .049 | 0.95        | 1.25  |
| E   | .620     | .635 | 15.75       | 16.13 |
| E1  | .516     | .557 | 13.10       | 14.15 |
| E2  | .145     | .201 | 3.68        | 5.10  |
| E3  | .039     | .075 | 1.00        | 1.90  |
| E4  | .487     | .529 | 12.38       | 13.43 |
| e   | .214 BSC |      | 5.44 BSC    |       |
| N   | 3        |      | 3           |       |
| L   | .780     | .800 | 19.81       | 20.32 |
| L1  | .161     | .173 | 4.10        | 4.40  |
| ØP  | .138     | .144 | 3.51        | 3.65  |
| Q   | .216     | .236 | 5.49        | 6.00  |
| S   | .238     | .248 | 6.04        | 6.30  |
| T   | 9°       | 11°  | 9°          | 11°   |
| U   | 9°       | 11°  | 9°          | 11°   |
| V   | 2°       | 8°   | 2°          | 8°    |
| W   | 2°       | 8°   | 2°          | 8°    |

NOTES:  
 ALL DIMENSIONS REFER TO JEDEC STANDARD TO-247 AND DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.  
 EJECTION MARK DEPTH 0.10<sup>+0.15</sup><sub>-0.10</sub>